

## **STATUS/AMENDMENTS OF THE CLAIMS:**

**1. (Currently Amended)** A semiconductor integrated circuit device comprising:

unit areas placed in plural form in a first direction;

a first line extending in the first direction over said plurality of unit areas;

a second line extending in the first direction along said plurality of unit areas and outside said plurality of unit areas; and

wiring areas provided adjacent to a first unit area of said plurality of unit areas and provided with a third line extending in a second direction, intersecting the first direction,

wherein said first unit area has a MOSFET formed therein,

wherein said third line ~~is used to connect~~ has a first terminal connected electrically to said second line and a second terminal connected electrically to a terminal of said MOSFET, and

wherein said third line is separated from said first line electrically.

**2. (Currently Amended)** A semiconductor integrated circuit device comprising:

unit areas placed in plural form in a first direction;

a first line, formed with a first layer, extending in the first direction over said plurality of unit areas;

a second line extending in the first direction along said plurality of unit areas and outside said plurality of unit areas; and

wiring areas provided adjacent to a first unit area of said plurality of unit areas and provided with a third line;

wherein said first unit area has a circuit formed therein,

wherein said third line connects has a first terminal connected electrically to said second line and a second terminal of connected electrically to said circuit,

wherein said third line is formed with a second layer which is different from said first layer, and

wherein said third line is separated from said first line electrically.

3. **(Original)** A semiconductor integrated circuit device according to claim 2,

wherein said second layer is formed by a single layer.